

Dual Series Switching Diode

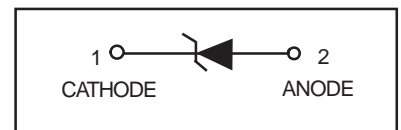
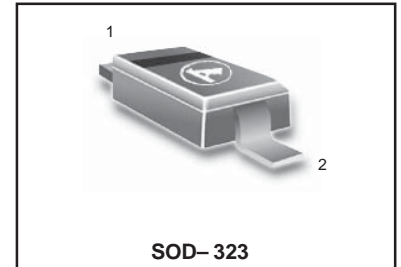
● FEATURES

- 1) Small plastic SMD package.
- 2) Continuous reverse voltage: max. 75 V.
- 3) High-speed switching in hybrid thick and thin-film circuits.
- 4) We declare that the material of product compliant with RoHS requirements and Halogen Free.
- 5) S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAS16HT1G	A6	3000/Tape&Reel
LBAS16HT3G	A6	10000/Tape&Reel

LBAS16HT1G S-LBAS16HT1G



● MAXIMUM RATINGS(T_a = 25°C)

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	75	Vdc
Peak Forward Current	I _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc

● THERMAL CHARACTERISTICS

Parameter Symbol	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board, (1) T _A = 25°C	P _D	200	mW
Derate above 25°C		1.57	mW/°C
Thermal Resistance Junction to Ambient	R _{θ JA}	635	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1.FR-4 Minimum Pad

● ELECTRICAL CHARACTERISTICS(T_A = 25°C unless otherwise noted) (EACH DIODE)

Parameter	Symbol	Min	Max.	Unit
Reverse Breakdown Voltage(I _{BR} =100μA)	V _(BR)	75	—	Vdc
Reverse Voltage Leakage Current (V _R =75Vdc)	I _R	—	1.0	μA
(V _R = 75 Vdc, T _J = 150°C)		—	50	
(V _R = 25 Vdc, T _J = 150°C)		—	30	
Diode Capacitance (V _R = 0, f = 1.0 MHz)	C _D	—	2.0	pF
Forward Voltage (I _F = 1.0 mAdc)	V _F	—	715	mVdc
(I _F = 10 mAdc)		—	855	
(I _F = 50 mAdc)		—	1000	
(I _F = 150 mAdc)		—	1250	
Forward Recovery Voltage (I _F = 10 mAdc, t _r = 20 ns)	V _{FR}	—	1.75	Vdc
Reverse Recovery Time (I _F =I _R =10mAd, R _L =50 Ω)	trr	—	4.0	ns
Stored Charge (I _F = 10 mAdc to V _R = 5.0 Vdc, R _L = 500 Ω)	Q _S	—	45	pC

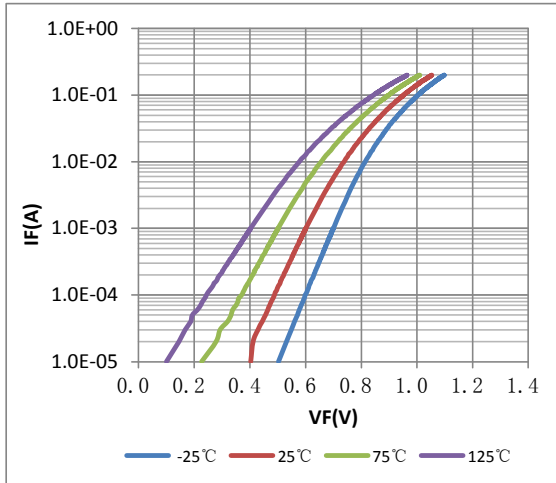
LBAS16HT1G,S-LBAS16HT1G
ELECTRICAL CHARACTERISTICS CURVES


FIG. 1 Forward Characteristics

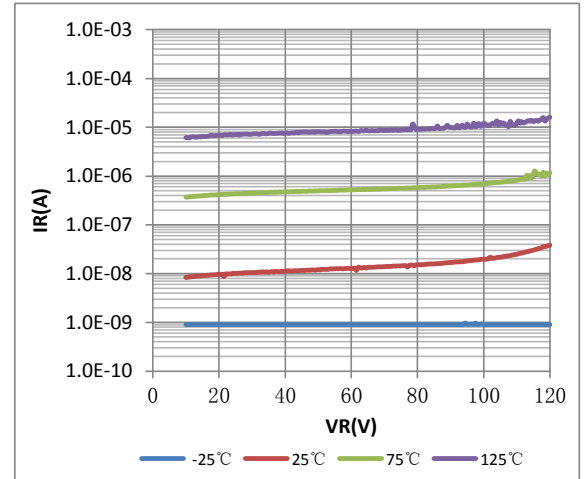


FIG. 2 Reverse Characteristics

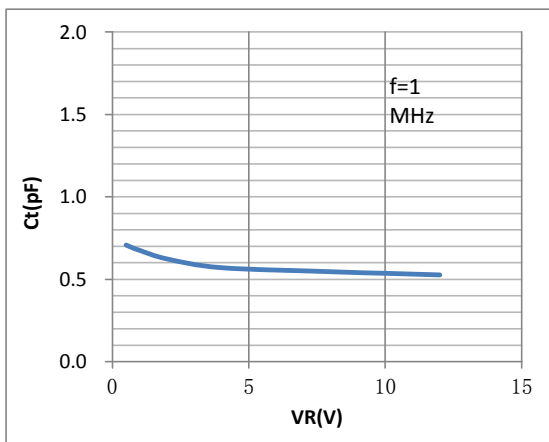
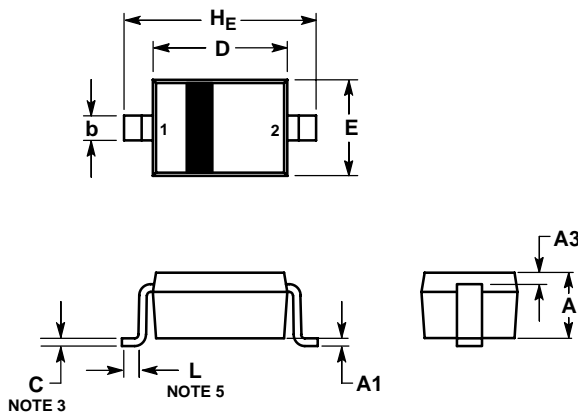


FIG. 3 Capacitance

LBAS16HT1G,S-LBAS16HT1G
SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*
